NSN 5961-01-414-5832

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Plastic

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-236ab

Mounting Method:

Terminal

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

30.0 reverse voltage, instantaneous

Current Rating Per Characteristic:

200.00 milliamperes source cutoff current preset

Power Rating Per Characteristic:

200.0 milliwatts small-signal input power, common-collector minor

Terminal Type And Quantity:

3 bonding pad

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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